

3.3V CMOS 10-BIT BUS-INTERFACE D-TYPE LATCH WITH 3-STATE OUTPUTS AND 5 VOLT TOLERANT I/O

FEATURES:

- 0.5 MICRON CMOS Technology
- ESD > 2000V per MIL-STD-883, Method 3015; > 200V using machine model (C = 200pF, R = 0)
- Vcc = 3.3V ± 0.3V, Normal Range
- Vcc = 2.7V to 3.6V, Extended Range
- CMOS power levels (0.4µ W typ. static)
- · Rail-to-rail output swing for increased noise margin
- All inputs, outputs, and I/O are 5V tolerant
- · Supports hot insertion
- · Available in SOIC, SSOP, QSOP, and TSSOP packages

DRIVE FEATURES:

- High Output Drivers: ±24mA
- Reduced system switching noise

APPLICATIONS:

- · 3.3V high speed systems
- · 3.3V and lower voltage computing systems

DESCRIPTION:

The LVC841A 10-bit bus-interface D-type latch is built using advanced dual metal CMOS technology. The LVC841A is designed specifically for driving highly capacitive or relatively low-impedance loads. It is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

The ten latches are transparent D-type latches. The device has noninverting data (D) inputs and provides true data at its outputs.

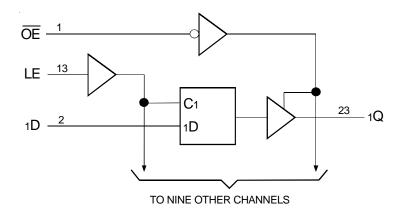
A buffered output-enable (\overline{OE}) input can be used to place the ten outputs in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components. \overline{OE} does not affect internal operations of the latch. Previously stored data can be retained or new data can be entered while the outputs are in the highimpedance state.

The LVC841A has been designed with a \pm 24mA output driver. This driver is capable of driving a moderate to heavy load while maintaining speed performance.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to Vcc through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Inputs can be driven from either 3.3V or 5V devices. This feature allows the use of this device as a translator in a mixed 3.3V/5V system environment.

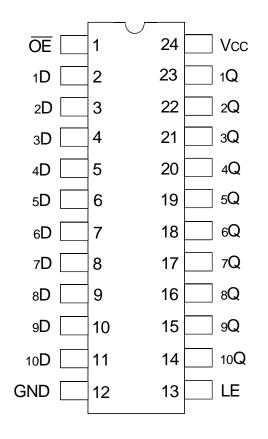
FUNCTIONAL BLOCK DIAGRAM



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INDUSTRIAL TEMPERATURE RANGE

PINCONFIGURATION



SOIC/ SSOP/ QSOP/ TSSOP TOP VIEW

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Description	Max	Unit
VTERM	Terminal Voltage with Respect to GND	-0.5 to +6.5	V
Tstg	Storage Temperature	–65 to +150	°C
Ιουτ	DC Output Current	-50 to +50	mA
Іік Іок	Continuous Clamp Current, VI < 0 or Vo < 0	-50	mA
lcc Iss	Continuous Current through each Vcc or GND	±100	mA

NOTE:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

CAPACITANCE (TA = +25°C, F = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Тур.	Max.	Unit
CIN	Input Capacitance	VIN = 0V	4.5	6	pF
Соит	Output Capacitance	Vout = 0V	5.5	8	pF
Ci/o	I/O Port Capacitance	VIN = 0V	6.5	8	pF

NOTE:

1. As applicable to the device type.

PINDESCRIPTION

Pin Names	Description
ŌĒ	Output Enable Control (Active LOW)
LE	Latch Enable Input
хD	Latch Data Inputs
хQ	3-State Latch Data Outputs

FUNCTION TABLE⁽¹⁾

Inputs			Outputs
хD	LE	ŌĒ	xQ
Н	Н	L	Н
L	Н	L	L
Х	L	L	Q ⁽²⁾
Х	Х	Н	Z

NOTES:

1. H = HIGH Voltage Level

L = LOW Voltage Level

X = Don't Care

Z = High Impedance

2. Output level before the indicated steady-state input conditions were established.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Operating Condition: $TA = -40^{\circ}C$ to $+85^{\circ}C$

Symbol	Parameter	Te	st Conditions	Min.	Тур. ⁽¹⁾	Max.	Unit
Vih	Input HIGH Voltage Level	Vcc = 2.3V to 2.7V		1.7	_	_	V
		Vcc = 2.7V to 3.6V		2	_	_	
Vil	Input LOW Voltage Level	Vcc = 2.3V to 2.7V		_	-	0.7	V
		Vcc = 2.7V to 3.6V		—	—	0.8	
lih lil	Input Leakage Current	Vcc = 3.6V	Vı = 0 to 5.5V	-	-	±5	μA
lozн lozl	High Impedance Output Current (3-State Output pins)	VCC = 3.6V	Vo = 0 to 5.5V	-	_	±10	μA
IOFF	Input/Output Power Off Leakage	Vcc = 0V, VIN or Vo \leq 5.5V		_	-	±50	μA
Vik	Clamp Diode Voltage	VCC = 2.3V, IIN = -18mA		_	-0.7	-1.2	V
Vн	Input Hysteresis	Vcc = 3.3V		_	100	_	mV
ICCL ICCH	Quiescent Power Supply Current	VCC = 3.6V	VIN = GND or Vcc	-	-	10	μA
lccz			$3.6 \le VIN \le 5.5V^{(2)}$	—	—	10	
Δlcc	Quiescent Power Supply Current Variation	One input at Vcc - 0.6V, o	other inputs at Vcc or GND	-	-	500	μA

NOTES:

1. Typical values are at Vcc = 3.3V, +25°C ambient.

2. This applies in the disabled state only.

OUTPUT DRIVE CHARACTERISTICS

Symbol	Parameter	TestCor	nditions ⁽¹⁾	Min.	Max.	Unit
Vон	Output HIGH Voltage	Vcc = 2.3V to 3.6V	Iон = - 0.1mA	Vcc-0.2	—	V
		Vcc = 2.3V	Iон = - 6mA	2	_	
		Vcc = 2.3V	Іон = – 12mA	1.7	_	
		Vcc = 2.7V		2.2	_	
		VCC = 3V	1	2.4	—	
		Vcc = 3V	Iон = - 24mA	2.2	—	
Vol	Output LOW Voltage	Vcc = 2.3V to 3.6V	IoL = 0.1mA	—	0.2	V
		Vcc = 2.3V	Iol = 6mA	_	0.4	
			IOL = 12mA	_	0.7	
		Vcc = 2.7V	Iol = 12mA	_	0.4	
		VCC = 3V	IOL = 24mA	_	0.55	

NOTE:

1. VIH and VIL must be within the min. or max. range shown in the DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE table for the appropriate Vcc range. TA = − 40°C to + 85°C.

OPERATING CHARACTERISTICS, VCC = 3.3V ± 0.3V, TA = 25°C

Symbol	Parameter	Test Conditions	Typical	Unit
Cpd	Power Dissipation Capacitance per Latch Outputs enabled	CL = 0pF, f = 10Mhz	25	pF
Cpd	Power Dissipation Capacitance per Latch Outputs disabled		6	

SWITCHING CHARACTERISTICS⁽¹⁾

		Vcc =	= 2.7V	Vcc = 3.3	V ± 0.3V	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
t PLH	Propagation Delay	—	7.5	2.4	6.7	ns
t PHL	xD to xQ					
t PLH	Propagation Delay	_	8.6	2.7	7.6	ns
t PHL	LE to xQ					
t PZH	Output Enable Time	_	8.5	1.3	7.2	ns
tPZL	OE to xQ					
tphz	Output Disable Time	_	6.6	1.9	5.9	ns
tPLZ	OE to xQ					
tw	Pulse Duration	3.3	_	3.3	_	ns
tsu	Set-up Time, data before LE↓	2.1	_	2.1	_	ns
tH	Hold Time, data after LE↓	1	_	1	_	ns
tsk(o)	Output Skew ⁽²⁾	—	—	—	1	ns

NOTES:

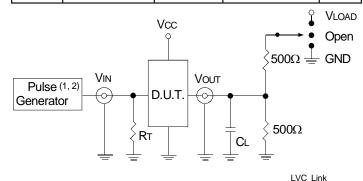
1. See TEST CIRCUITS AND WAVEFORMS. TA = -40° C to $+85^{\circ}$ C.

2. Skew between any two outputs of the same package and switching in the same direction.

IDT74LVC841A 3.3VCMOS10-BITBUS-INTERFACED-TYPE LATCH

TEST CIRCUITS AND WAVEFORMS TEST CONDITIONS

Symbol	$Vcc^{(1)} = 3.3V \pm 0.3V$	Vcc ⁽¹⁾ =2.7V	Vcc ⁽²⁾ =2.5V±0.2V	Unit		
Vload	6	6	2 x Vcc	V		
Vih	2.7	2.7	Vcc	V		
Vт	1.5	1.5	Vcc / 2	V		
Vlz	300	300	150	mV		
Vhz	300	300	150	mV		
CL	50	50	30	pF		



Test Circuit for All Outputs

DEFINITIONS:

CL = Load capacitance: includes jig and probe capacitance.

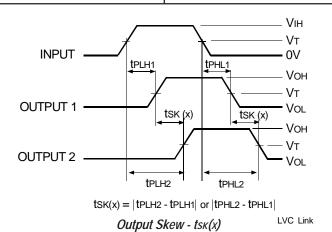
RT = Termination resistance: should be equal to ZOUT of the Pulse Generator.

NOTES:

1. Pulse Generator for All Pulses: Rate \leq 10MHz; tF \leq 2.5ns; tR \leq 2.5ns. 2. Pulse Generator for All Pulses: Rate \leq 10MHz; tF \leq 2ns; tR \leq 2ns.

SWITCH POSITION

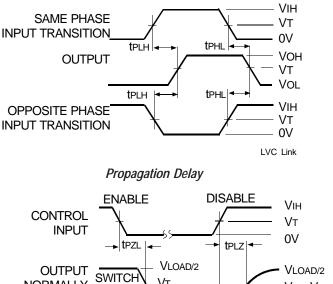
Test	Switch
Open Drain Disable Low Enable Low	Vload
Disable High Enable High	GND
All Other Tests	Open

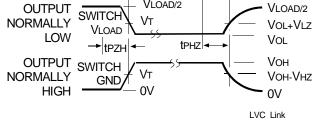


NOTES:

1. For tsk(o) OUTPUT1 and OUTPUT2 are any two outputs.

2. For tsk(b) OUTPUT1 and OUTPUT2 are in the same bank.

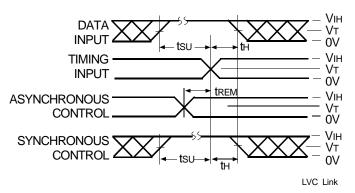


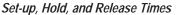


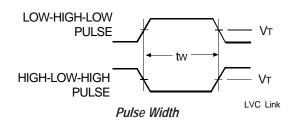
Enable and Disable Times

NOTE:

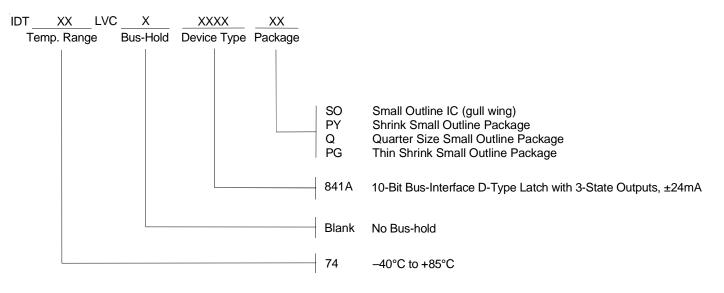
1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.







ORDERING INFORMATION





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